



ON Semiconductor®

## ISL9V5036S3S / ISL9V5036P3 / ISL9V5036S3

### EcoSPARK® 500mJ, 360V, N-Channel Ignition IGBT

#### General Description

The ISL9V5036S3S, ISL9V5036P3, and ISL9V5036S3 are the next generation IGBTs that offer outstanding SCIS capability in the D<sup>2</sup>-Pak (TO-263) and TO-220 plastic package. These devices are intended for use in automotive ignition circuits, specifically as coil drivers. Internal diodes provide voltage clamping without the need for external components.

**EcoSPARK®** devices can be custom made to specific clamp voltages. Contact your nearest ON Semiconductor sales office for more information.

Formerly Developmental Type 49443

#### Applications

- Automotive Ignition Coil Driver Circuits
- Coil-On Plug Applications

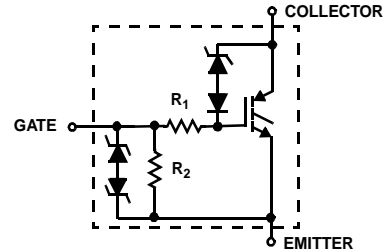
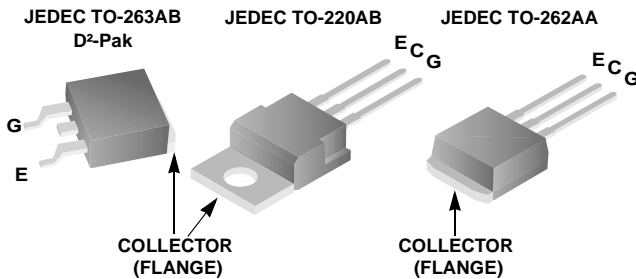
#### Features

- Industry Standard D<sup>2</sup>-Pak package
- SCIS Energy = 500mJ at  $T_J = 25^\circ\text{C}$
- Logic Level Gate Drive
- Qualified to AEC Q101
- RoHS Compliant



#### Package

#### Symbol



#### Device Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$BV_{CER}$	Collector to Emitter Breakdown Voltage ( $I_C = 1\text{ mA}$ )	390	V
$BV_{ECS}$	Emitter to Collector Voltage - Reverse Battery Condition ( $I_C = 10\text{ mA}$ )	24	V
$E_{SCIS25}$	At Starting $T_J = 25^\circ\text{C}$ , $I_{SCIS} = 38.5\text{ A}$ , $L = 670\text{ }\mu\text{H}$	500	mJ
$E_{SCIS150}$	At Starting $T_J = 150^\circ\text{C}$ , $I_{SCIS} = 30\text{ A}$ , $L = 670\text{ }\mu\text{H}$	300	mJ
$I_{C25}$	Collector Current Continuous, At $T_C = 25^\circ\text{C}$ , See Fig 9	46	A
$I_{C110}$	Collector Current Continuous, At $T_C = 110^\circ\text{C}$ , See Fig 9	31	A
$V_{GEM}$	Gate to Emitter Voltage Continuous	$\pm 10$	V
$P_D$	Power Dissipation Total $T_C = 25^\circ\text{C}$	250	W
	Power Dissipation Derating $T_C > 25^\circ\text{C}$	1.67	W/ $^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-40 to 175	$^\circ\text{C}$
$T_{STG}$	Storage Junction Temperature Range	-40 to 175	$^\circ\text{C}$
$T_L$	Max Lead Temp for Soldering (Leads at 1.6mm from Case for 10s)	300	$^\circ\text{C}$
$T_{pkg}$	Max Lead Temp for Soldering (Package Body for 10s)	260	$^\circ\text{C}$
ESD	Electrostatic Discharge Voltage at 100pF, 1500 $\Omega$	4	kV

**Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
V5036S	ISL9V5036S3ST	TO-263AB	330mm	24mm	800
V5036P	ISL9V5036P3	TO-220AA	Tube	N/A	50
V5036S	ISL9V5036S3	TO-262AA	Tube	N/A	50
V5036S	ISL9V5036S3S	TO-263AB	Tube	N/A	50

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off State Characteristics**

$BV_{CER}$	Collector to Emitter Breakdown Voltage	$I_C = 2\text{mA}$ , $V_{GE} = 0$ , $R_G = 1\text{K}\Omega$ , See Fig. 15 $T_J = -40$ to $150^\circ\text{C}$	330	360	390	V
$BV_{CES}$	Collector to Emitter Breakdown Voltage	$I_C = 10\text{mA}$ , $V_{GE} = 0$ , $R_G = 0$ , See Fig. 15 $T_J = -40$ to $150^\circ\text{C}$	360	390	420	V
$BV_{ECS}$	Emitter to Collector Breakdown Voltage	$I_C = -75\text{mA}$ , $V_{GE} = 0\text{V}$ , $T_C = 25^\circ\text{C}$	30	-	-	V
$BV_{GES}$	Gate to Emitter Breakdown Voltage	$I_{GES} = \pm 2\text{mA}$	$\pm 12$	$\pm 14$	-	V
$I_{CER}$	Collector to Emitter Leakage Current	$V_{CER} = 250\text{V}$ , $R_G = 1\text{K}\Omega$ , See Fig. 11	$T_C = 25^\circ\text{C}$	-	-	25 $\mu\text{A}$
			$T_C = 150^\circ\text{C}$	-	-	1 mA
$I_{ECS}$	Emitter to Collector Leakage Current	$V_{EC} = 24\text{V}$ , See Fig. 11	$T_C = 25^\circ\text{C}$	-	-	1 mA
			$T_C = 150^\circ\text{C}$	-	-	40 mA
$R_1$	Series Gate Resistance		-	75	-	$\Omega$
$R_2$	Gate to Emitter Resistance		10K	-	30K	$\Omega$

**On State Characteristics**

$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	$I_C = 10\text{A}$ , $V_{GE} = 4.0\text{V}$	$T_C = 25^\circ\text{C}$ , See Fig. 4	-	1.17	1.60	V
$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	$I_C = 15\text{A}$ , $V_{GE} = 4.5\text{V}$	$T_C = 150^\circ\text{C}$	-	1.50	1.80	V

**Dynamic Characteristics**

$Q_{G(ON)}$	Gate Charge	$I_C = 10A, V_{CE} = 12V,$ $V_{GE} = 5V, \text{ See Fig. 14}$		-	32	-	nC
$V_{GE(TH)}$	Gate to Emitter Threshold Voltage	$I_C = 1.0mA,$ $V_{CE} = V_{GE},$ See Fig. 10	$T_C = 25^{\circ}C$	1.3	-	2.2	V
			$T_C = 150^{\circ}C$	0.75	-	1.8	V
$V_{GEP}$	Gate to Emitter Plateau Voltage	$I_C = 10A,$	$V_{CE} = 12V$	-	3.0	-	V

**Switching Characteristics**

$t_{d(ON)R}$	Current Turn-On Delay Time-Resistive	$V_{CE} = 14\text{V}$ , $R_L = 1\Omega$ , $V_{GE} = 5\text{V}$ , $R_G = 1\text{K}\Omega$ , $T_J = 25^\circ\text{C}$ , See Fig. 12	-	0.7	4	$\mu\text{s}$
$t_{rR}$	Current Rise Time-Resistive		-	2.1	7	$\mu\text{s}$
$t_{d(OFF)L}$	Current Turn-Off Delay Time-Inductive	$V_{CE} = 300\text{V}$ , $L = 2\text{mH}$ , $V_{GE} = 5\text{V}$ , $R_G = 1\text{K}\Omega$ , $T_J = 25^\circ\text{C}$ , See Fig. 12	-	10.8	15	$\mu\text{s}$
$t_{fL}$	Current Fall Time-Inductive		-	2.8	15	$\mu\text{s}$
SCIS	Self Clamped Inductive Switching	$T_J = 25^\circ\text{C}$ , $L = 670\mu\text{H}$ , $R_G = 1\text{K}\Omega$ , $V_{GE} = 5\text{V}$ , See Fig. 1 & 2	-	-	500	mJ

**Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance Junction-Case	TO-263, TO-220, TO-262	-	-	0.6	$^\circ\text{C/W}$
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## Typical Characteristics

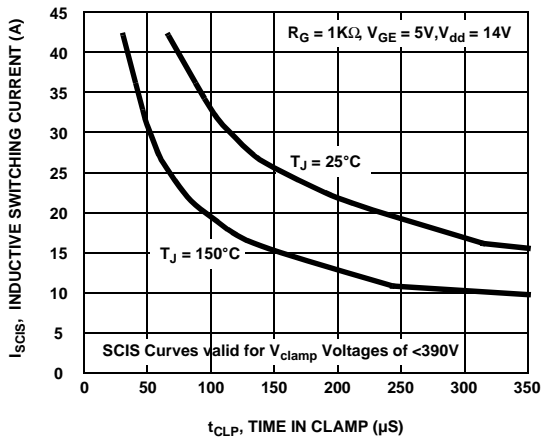


Figure 1. Self Clamped Inductive Switching Current vs Time in Clamp

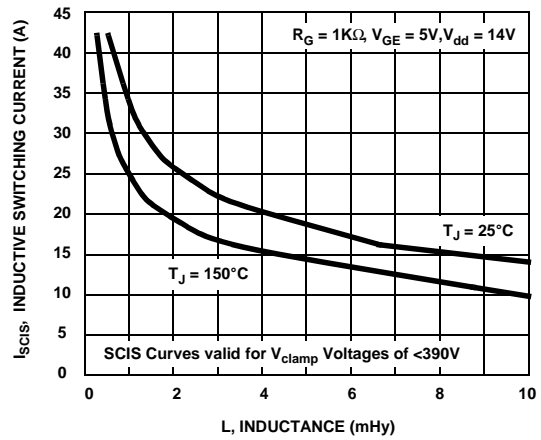


Figure 2. Self Clamped Inductive Switching Current vs Inductance

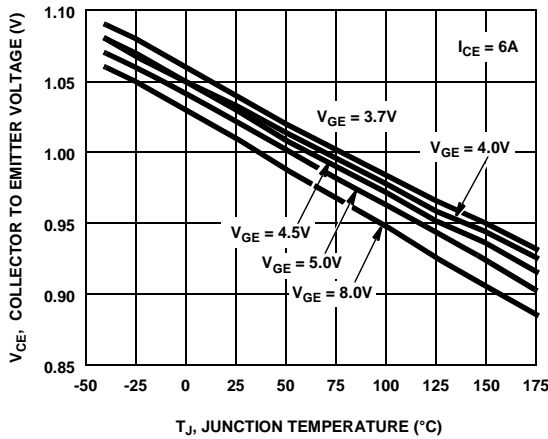


Figure 3. Collector to Emitter On-State Voltage vs Junction Temperature

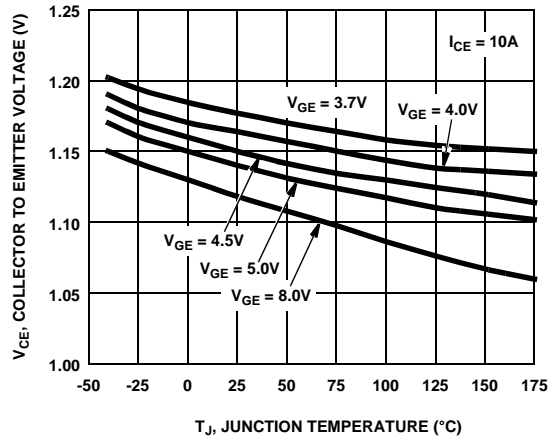


Figure 4. Collector to Emitter On-State Voltage vs Junction Temperature

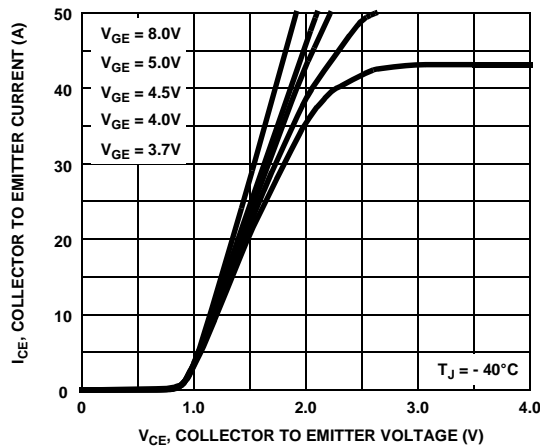


Figure 5. Collector Current vs Collector to Emitter On-State Voltage

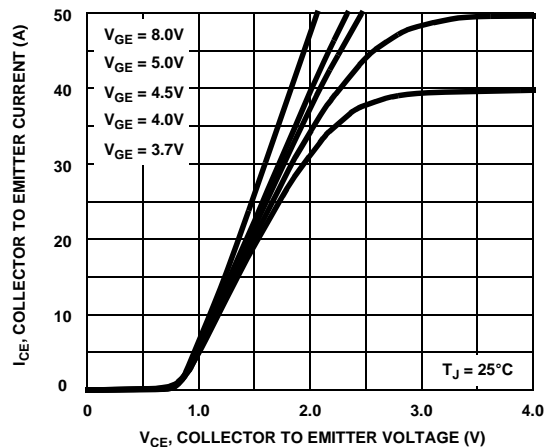


Figure 6. Collector Current vs Collector to Emitter On-State Voltage

## Typical Characteristics (Continued)

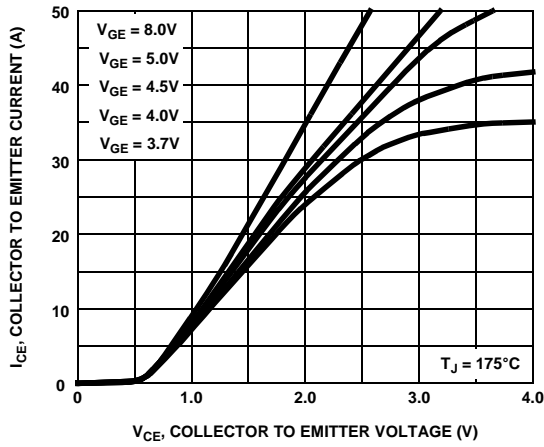


Figure 7. Collector to Emitter On-State Voltage vs Collector Current

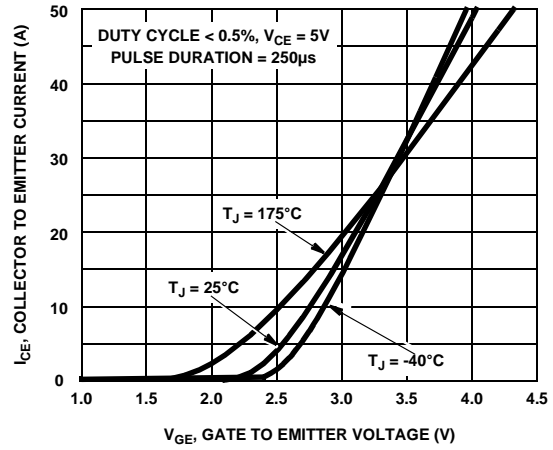


Figure 8. Transfer Characteristics

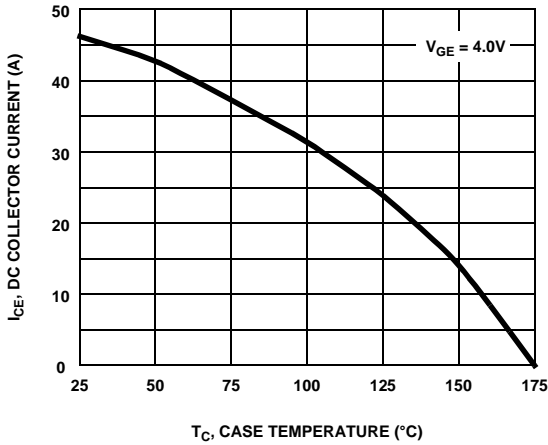


Figure 9. DC Collector Current vs Case Temperature

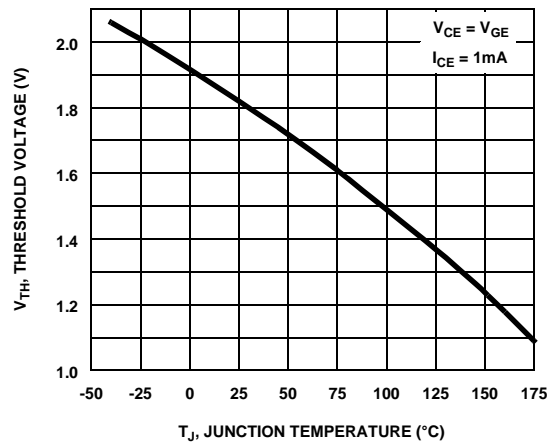


Figure 10. Threshold Voltage vs Junction Temperature

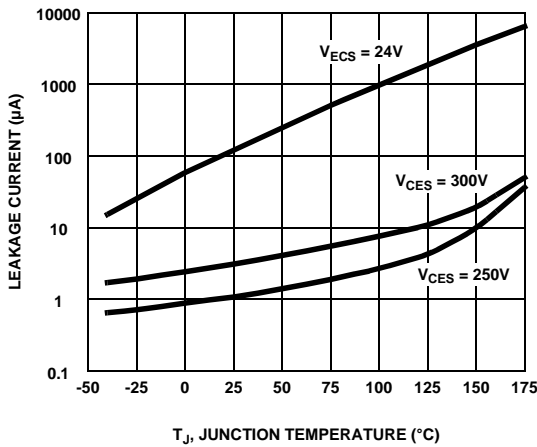


Figure 11. Leakage Current vs Junction Temperature

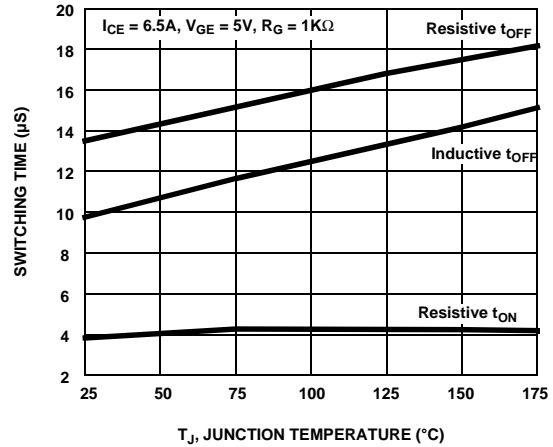


Figure 12. Switching Time vs Junction Temperature

## Typical Characteristics (Continued)

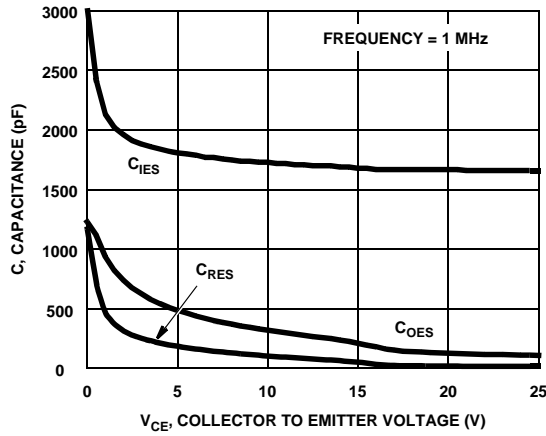


Figure 13. Capacitance vs Collector to Emitter Voltage

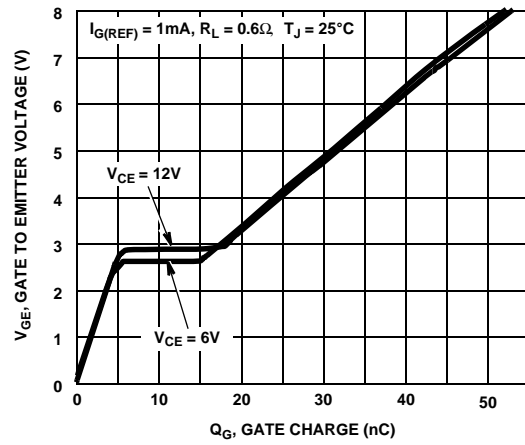


Figure 14. Gate Charge

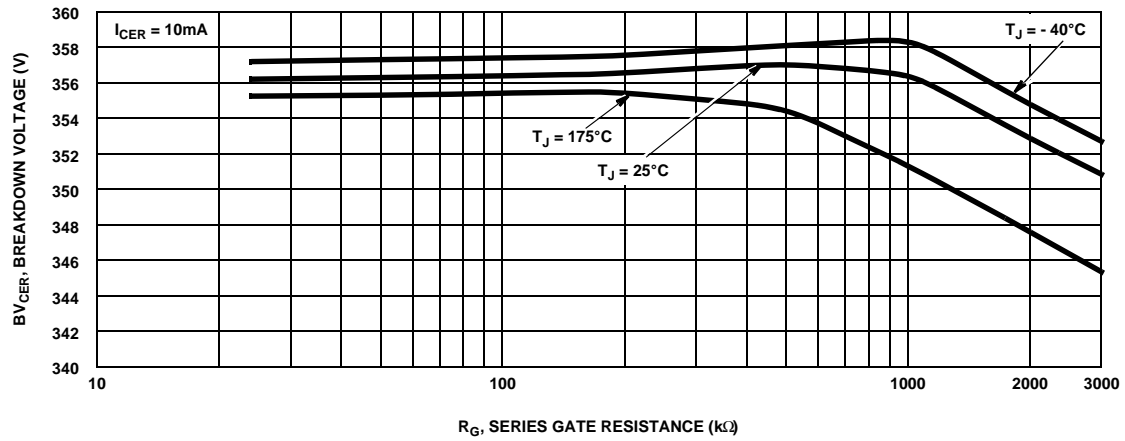


Figure 15. Breakdown Voltage vs Series Gate Resistance

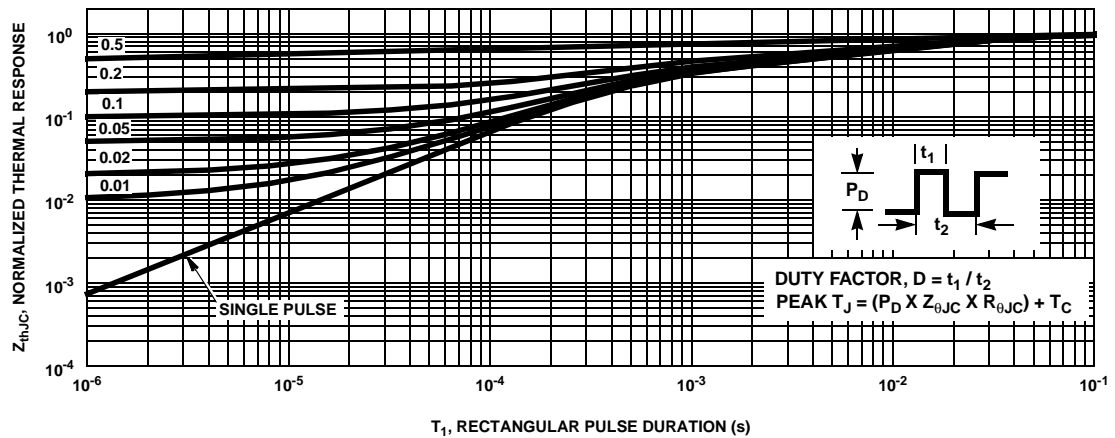


Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case

## Test Circuits and Waveforms

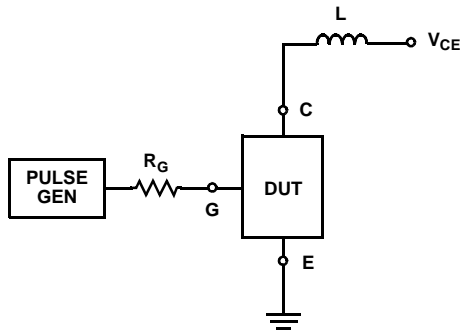


Figure 17. Inductive Switching Test Circuit

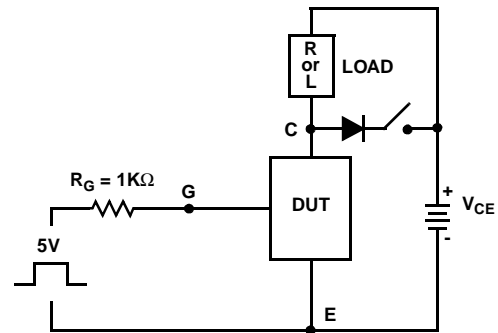


Figure 18.  $t_{ON}$  and  $t_{OFF}$  Switching Test Circuit

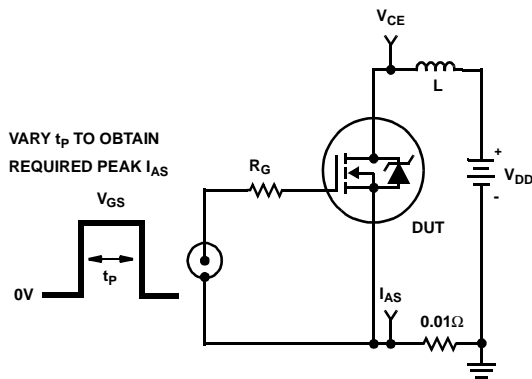


Figure 19. Energy Test Circuit

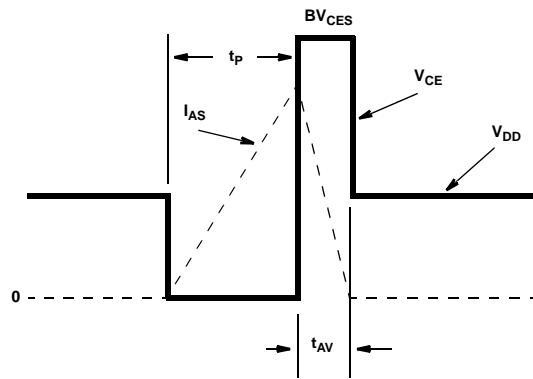


Figure 20. Energy Waveforms

## SPICE Thermal Model

REV 1 May 2002

ISL9V5036S3S / ISL9V3536P3 / ISL9V5036S3

CTHERM1 th 6 4.0e2  
CTHERM2 6 5 3.6e-3  
CTHERM3 5 4 4.9e-2  
CTHERM4 4 3 3.2e-1  
CTHERM5 3 2 3.0e-1  
CTHERM6 2 tl 1.6e-2

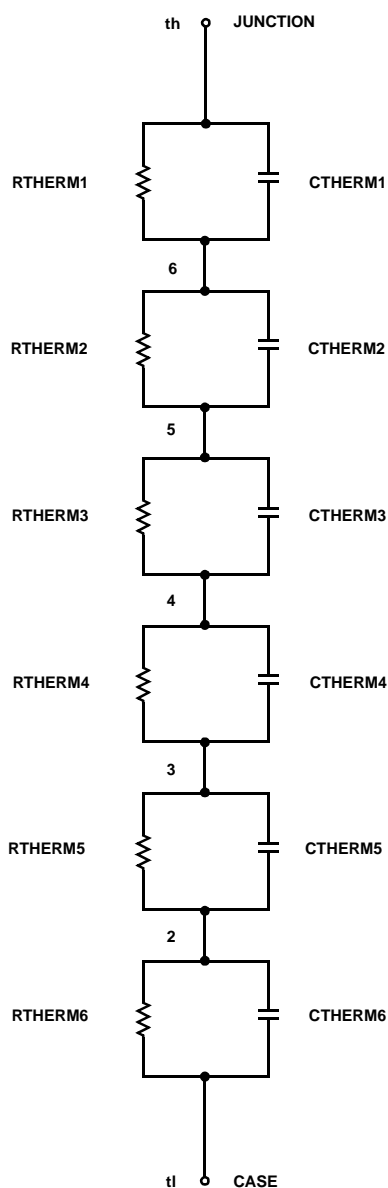
RTHERM1 th 6 1.0e-2  
RTHERM2 6 5 1.4e-1  
RTHERM3 5 4 1.0e-1  
RTHERM4 4 3 9.0e-2  
RTHERM5 3 2 9.4e-2  
RTHERM6 2 tl 1.9e-2

## SABER Thermal Model

SABER thermal model  
ISL9V5036S3S / ISL9V5036P3 / ISL9V5036S3  
template thermal\_model th tl  
thermal\_c th, tl

```
{
  ctherm.ctherm1 th 6 = 4.0e2
  ctherm.ctherm2 6 5 = 3.6e-3
  ctherm.ctherm3 5 4 = 4.9e-2
  ctherm.ctherm4 4 3 = 3.2e-1
  ctherm.ctherm5 3 2 = 3.0e-1
  ctherm.ctherm6 2 tl = 1.6e-2
```

```
  rtherm.rtherm1 th 6 = 1.0e-2
  rtherm.rtherm2 6 5 = 1.4e-1
  rtherm.rtherm3 5 4 = 1.0e-1
  rtherm.rtherm4 4 3 = 9.0e-2
  rtherm.rtherm5 3 2 = 9.4e-2
  rtherm.rtherm6 2 tl = 1.9e-2
}
```



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